

TIP140/141/142 TIP145/146/147

COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

- TIP141, TIP142, TIP145 AND TIP147 ARE STMicroelectronics PREFERRED SALESTYPES
- COMPLEMENTARY PNP NPN DEVICES
- MONOLITHIC DARLINGTON CONFIGURATION
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE

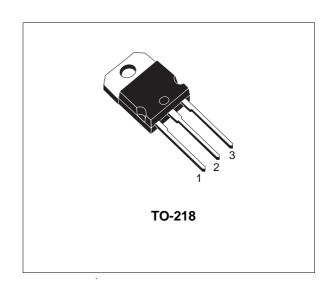
APPLICATIONS

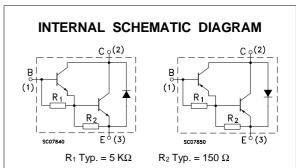
 LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT

DESCRIPTION

The TIP140, TIP141 and TIP142 are silicon Epitaxial-Base NPN power transistors in monolithic Darlington configuration, mounted in TO-218 plastic package. They are intented for use in power linear and switching applications.

The complementary PNP types are TIP145, TIP146 and TIP147 respectively.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value			Unit
		NPN	TIP140	TIP141	TIP142	
		PNP	TIP145	TIP146	TIP147	
V _{CBO}	Collector-Base Voltage (I _E = 0)	·	60	80	100	V
V_{CEO}	Collector-Emitter Voltage (I _B = 0)		60	80	100	V
V_{EBO}	Emitter-Base Voltage (I _C = 0)			5	•	V
Ic	Collector Current			10		Α
I _{CM}	Collector Peak Current			20		Α
I_B	Base Current			0.5		Α
P_{tot}	Total Dissipation at T _{case} ≤ 25 °C			125		W
T_{stg}	Storage Temperature			-65 to 150		°C
Tj	Max. Operating Junction Temperature		·	150		°C

For PNP types voltage and current values are negative.

March 2000 1/4

TIP140 / TIP141 / TIP142 / TIP145 / TIP146 / TIP147

THERMAL DATA

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

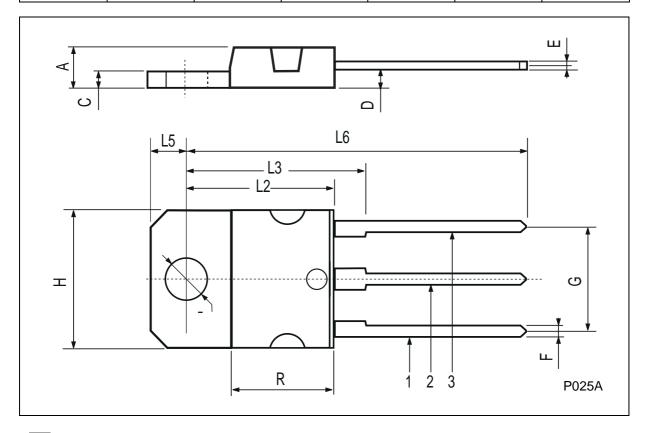
Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	for TIP140/145 for TIP141/146 for TIP142/147	V _{CB} = 60 V V _{CB} = 80 V V _{CB} = 100 V			1 1 1	mA mA mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	for TIP140/145 for TIP141/146 for TIP142/147	V _{CE} = 30 V V _{CE} = 40 V V _{CE} = 50 V			2 2 2	mA mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V				2	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA for TIP140/145 for TIP141/146 for TIP142/147		60 80 100			V V V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 5 A I _C = 10 A	I _B = 10 mA I _B = 40 mA			2 3	V V
V _{BE(on)} *	Base-Emitter Voltage	I _C = 10 A	V _{CE} = 4 V			3	V
h _{FE} *	DC Current Gain	I _C = 5 A I _C = 10 A	V _{CE} = 4 V V _{CE} = 4 V	1000 500			
t _{on} t _{off}	RESISTIVE LOAD Turn-on Time Turn-off Time	I _C = 10 A I _{B2} = -40 mA	I_{B1} = 40 mA R_L = 3 Ω		0.9 4		μs μs

For PNP types voltage and current values are negative.

* Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

TO-218 (SOT-93) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	4.7		4.9	0.185		0.193
С	1.17		1.37	0.046		0.054
D		2.5			0.098	
E	0.5		0.78	0.019		0.030
F	1.1		1.3	0.043		0.051
G	10.8		11.1	0.425		0.437
Н	14.7		15.2	0.578		0.598
L2	_		16.2	_		0.637
L3		18			0.708	
L5	3.95		4.15	0.155		0.163
L6		31			1.220	
R	-		12.2	_		0.480
Ø	4		4.1	0.157		0.161



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 2000 STMicroelectronics - Printed in Italy - All Rights Reserved STMicroelectronics GROUP OF COMPANIES Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A.

http://www.st.com

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.